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DB=USPT; PLUR=YES; OP=OR

L10   L9 and substrate and silicon1250   L10L9   "(110)".clm.10952   L9L8   L7 and ((hydrogenated near4 nitride) or (oxynitride))94   L8L7   glass with ((passivation or base or underlayer or blocking) near4 (layer or film)) and (TFT\$1 or (thin adj film))2025   L7L6   fonash.in.18   L6L5   L4 not (semiconductor and energy and laboratory)105   L5L4   L3 and semiconductor365   L4L3   L2 and oxide1174   L3L2   L1 and (nickel with solution)1318   L2L1   amorphous same crystal\$840932   L1

END OF SEARCH HISTORY